Ref #	Hits	Search Query	DBs	Default Operator	Plurais	Time Stamp
L1	109	LDMOS and epitaxial and boron and arsenic and LOCOS and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 13:52
L2	2	1 and photoresist and bak\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 13:53
L3	22	1 and photoresist and develop\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 13:56
L4	49	1 and photoresist and anneal\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 13:56
L5	1	1 and photoresist and anneal\$4 and bake	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 13:57
L6	2	1 and photoresist and bake	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 13:57
L7		1 and photoresist and baking	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 13:57
L8	16	1 and photoresist and hard	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 13:59

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L9	3	1 and photoresist with hard	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:00
L10	1044	257/341.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:00
L11	130	438/135.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:00
L12	613	438/306.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:00
L13	781	438/527.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:22
L14	1297	photoresist with hard adj bak\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:01
L15	2	photoresist with hard adj bak\$4 same implant\$3 with arsenic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:01
L16	2	photoresist with hard adj bak\$4 same implant\$3 with "As"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:02

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L17	33	photoresist with hard adj bak\$4 same implant\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:09
L18	2	17 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:36
L19	8	photoresist with hard adj bak\$4 same implant\$3 and epitaxial	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:20
L20	1	((soft adj bak\$4 same implant\$4 with boron) and (hard adj bak\$4 same implant\$4 with Arsenic))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:21
L21	2	((photoresist same implant\$4 with boron) and (hard adj bak\$4 same implant\$4 with Arsenic))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:21
L22	1371	438/217.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:22
L23	587	438/231.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:22
L24	370	438/294.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:23

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L25	1341	438/303.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:23
L27	905	257/335.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:23
L28	2278	438/305.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:24
L29	0	10 and (resist or photoresist or mask) with hard adj bak\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:25
L30	0	10 and (resist or photoresist or mask) and hard adj bak\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:25
L31	1	11 and (resist or photoresist or mask) and hard adj bak\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:36
L32	5	12 and (resist or photoresist or mask) and hard adj bak\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:35
L33	5	13 and (resist or photoresist or mask) and hard adj bak\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:25

L34	1	22 and (resist or photoresist or mask) and hard adj bak\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:26
L35	5	23 and (resist or photoresist or mask) and hard adj bak\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:35
L36	2	24 and (resist or photoresist or mask) and hard adj bak\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:26
L37	5	25 and (resist or photoresist or mask) and hard adj bak\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:35
L38	1	27 and (resist or photoresist or mask) and hard adj bak\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:36
L39	5	28 and (resist or photoresist or mask) and hard adj bak\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:26
L40	1	31 and (implant\$4 with (arsenic or "As"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:35
L41	5	32 and (implant\$4 with (arsenic or "As"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:27

L42	4	33 and (implant\$4 with (arsenic or "As"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:27
L43	1	34 and (implant\$4 with (arsenic or "As"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:27
L44	, 4	35 and (implant\$4 with (arsenic or "As"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:35
L45	2	36 and (implant\$4 with (arsenic or "As"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:35
L46	5	37 and (implant\$4 with (arsenic or "As"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:34
L47	1	38 and (implant\$4 with (arsenic or "As"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:28
L48	4	39 and (implant\$4 with (arsenic or "As"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:29
L49	1	40 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:30

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L50	1	41 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:34
L51	2	42 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:30
L52	0	43 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:29
L53	0	44 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:30
L54	1	45 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:30
L55	0	46 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:30
L56	0	47 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 14:30

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S82	25	(epitaxial with deep) and (resist or mask or photoresist) and (boron or "B") and ("As" or arsenic) and LOCOS and gate adj dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:14
S83	19	(epitaxial with deep same "N") and (resist or mask or photoresist) and (boron or "B") and ("As" or arsenic) and LOCOS and gate adj dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:14
S84	8	S83 and (bak\$4 or anneal\$3 or develop\$3)with (resist or photoresist or mask)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:16
S85	4	S84 and ("N" with deep with ("As" or arsenic))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:18
S86	130	438/135.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:19
S87	613	438/306.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:19
S88	781	438/527.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:19
S89	9	Hu.in. and deep with epitaxial	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:20

S90	49	Lee.in. and deep with epitaxial	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:28
S91	15	Edwards.in. and deep with epitaxial	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:29
S92	13	Lin.in. and deep with epitaxial	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:30
S93	0	Bolkhavsky.in. and deep with epitaxial	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:31
S94	289	shallow and deep with epitaxial with "N"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:31
S95	73	shallow with deep with epitaxial with "N"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:31
S96	5	S95 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:33
S97	126	double with diffus\$4 with "N" same deep	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:37

S98	26	S97 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO;	OR	ON	2006/07/21 11:34
S99	19	S98 and (resist or mask or photoresist)	DERWENT; IBM_TDB US-PGPUB; USPAT;	OR	ON	2006/07/21 11:35
		photorcascy	USOCR; EPO; JPO; DERWENT; IBM_TDB			
S10 0	26	double with diffus\$4 with "N" same deep same epitaxial\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:37
S10 1	6	S100 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/21 11:37